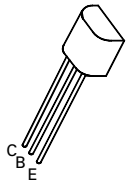
PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

ZTX550 ZTX551

ISSUE 1 – MARCH 94

FEATURES

* 60 Volt V_{CEO}
* 1 Amp continuous current
* P_{tot}= 1 Watt



E-Line
TO92 Compatible

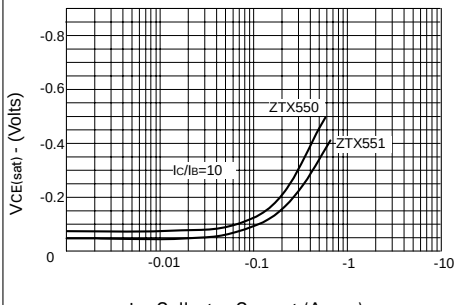
ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	ZTX550	ZTX551	UNIT
Collector-Base Voltage	V_{CBO}	-60	-80	V
Collector-Emitter Voltage	V_{CEO}	-45	-60	V
Emitter-Base Voltage	V_{EBO}	-5		V
Peak Pulse Current	I_{CM}	-2		A
Continuous Collector Current	I_C	-1		A
Power Dissipation: at T_{amb}=25°C derate above 25°C	P_{tot}	1 5.7		W mW/ °C
Operating and Storage Temperature Range	T_j:T_{stg}	-55 to +200		°C

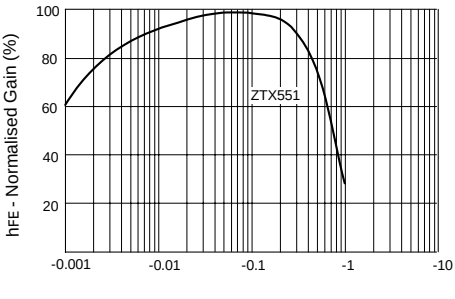
ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C).

PARAMETER	SYMBOL	ZTX550		ZTX551		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60		-80		V	I_C=-100μA
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	-45		-60		V	I_C=-10mA*
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		-5		V	I_E=-100μA
Collector Cut-Off Current	I_{CBO}		-0.1		-0.1	μA μA	V_{CB}=-45V V_{CB}=-60V
Emitter Cut-Off Current	I_{EBO}		-0.1		-0.1	μA	V_{EB}=-4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.25		-0.35	V	I_C=-150mA, I_B=-15mA*
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.1		-1.1	V	I_C=-150mA, I_B=-15mA*
Static Forward Current Transfer Ratio	h_{FE}	100 15	300	50 10	150		I_C=-150mA, V_{CE}=-10V* I_C=-1A, V_{CE}=-10V*
Transition Frequency	f_T	150		150		MHz	I_C=-50mA, V_{CE}=-10V f=100MHz

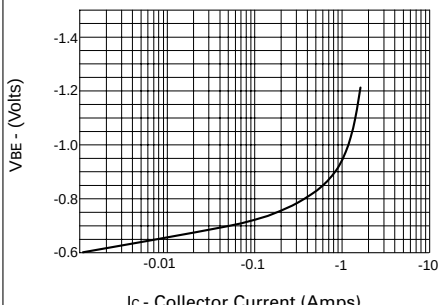
TYPICAL CHARACTERISTICS



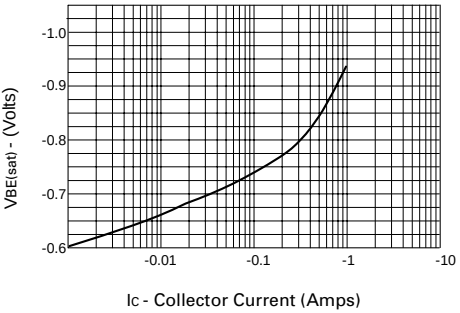
VCE(sat) v IC



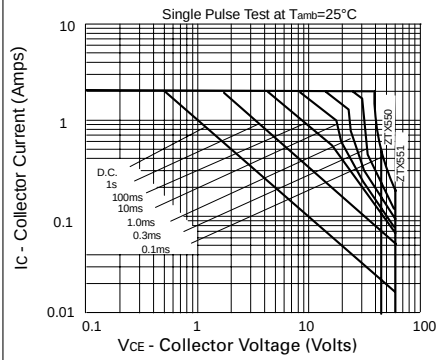
hFE v IC



VBE(on) v IC



VBE(sat) v IC



Safe Operating Area